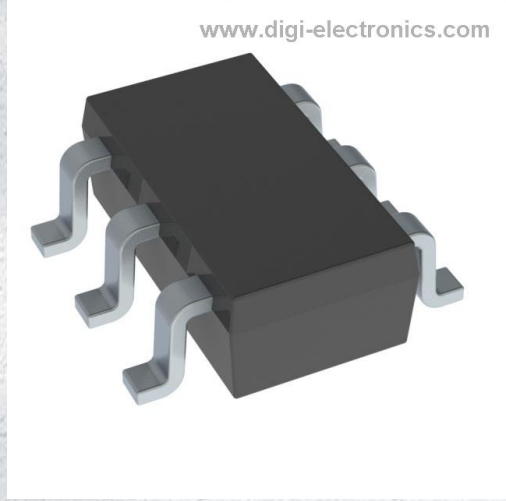
SI3430DV-T1-E3 Datasheet



DiGi Electronics Part Number	SI3430DV-T1-E3-DG
Manufacturer	Vishay Siliconix
Manufacturer Product Number	SI3430DV-T1-E3
Description	MOSFET N-CH 100V 1.8A 6TSOP
Detailed Description	N-Channel 100 V 1.8A (Ta) 1.14W (Ta) Surface Mount 6-TSOP

https://www.DiGi-Electronics.com

Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

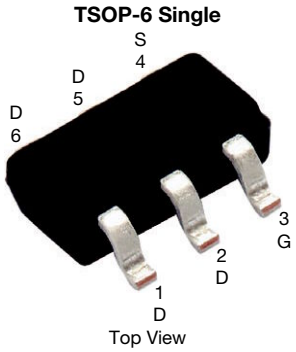
Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
SI3430DV-T1-E3	Vishay Siliconix
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
100 V	1.8A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
6V, 10V	170mOhm @ 2.4A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 250µA (Min)	6.6 nC @ 10 V
Vgs (Max):	FET Feature:
±20V	-
Power Dissipation (Max):	Operating Temperature:
1.14W (Ta)	-55°C ~ 150°C (TJ)
Mounting Type:	Supplier Device Package:
Surface Mount	6-TSOP
Package / Case:	Base Product Number:
SOT-23-6 Thin, TSOT-23-6	SI3430

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	

N-Channel 100 V (D-S) MOSFET



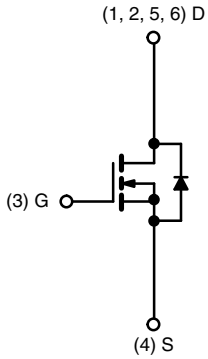
FEATURES

- High-efficiency PWM optimized
- 100 % R_g tested
- Material categorization:
  for definitions of compliance please see
  www.vishay.com/doc?99912

Pb-free

RoHS COMPLIANT

HALOGEN FREE Available



N-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	100
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.170
$R_{DS(on)}$ max. (Ω) at V_{GS} = 6 V	0.185
Q_g typ. (nC)	5.5
I_D (A)	2.4
Configuration	Single

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free	Si3430DV-T1-E3
Lead (Pb)-free and halogen-free	Si3430DV-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	5 s	STEADY STATE	UNIT
Drain-source voltage		V_{DS}	100	100	V
Gate-source voltage		V_{GS}	± 20	± 20	
Continuous drain current (T_J = 175 °C) [a]	T_A = 25 °C	I_D	2.4	1.8	A
	T_A = 85 °C		1.7	1.3	
Pulsed drain current		I_{DM}	8	8	
Avalanche current	L = 0.1 mH	I_{AR}	6	6	
Repetitive avalanche energy (duty cycle ≤ 1 %)		E_{AR}	1.8	1.8	mJ
Continuous source current (diode conduction) [a]		I_S	1.7	1	A
Maximum power dissipation [a]	T_A = 25 °C	P_D	2	1.14	W
	T_A = 85 °C		1	0.59	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	-55 to +150	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient [a]	t ≤ 5 s	R_{thJA}	45	62.5	°C/W
	Steady state		90	110	
Maximum junction-to-foot (drain)	Steady state	Rt_{hJF}	25	30	

Note

a. Surface mounted on 1" x 1" FR4 board

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = V_{DS}, I_D = 250 µA	2	-	4.2	V
Gate-body leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 80 V, V_{GS} = 0 V	-	-	1	µA
		V_{DS} = 80 V, V_{GS} = 0 V, T_J = 85 °C	-	-	25	
On-state drain current [a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	8	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 2.4 A	-	0.148	0.170	Ω
		V_{GS} = 6 V, I_D = 2.3 A	-	0.160	0.185	
Forward transconductance [a]	g_{fs}	V_{DS} = 15 V, I_D = 2.4 A	-	7	-	S
Diode forward voltage [a]	V_{SD}	I_S= 1.7 A, V_{GS} = 0 V	-	0.8	1.2	V
Dynamic [b]						
Total gate charge	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 2.4 A	-	5.5	8.2	nC
Gate-source charge	Q_{gs}		-	1.5	-	
Gate-drain charge	Q_{gd}		-	1.4	-	
Gate resistance	R_g		1	-	4	Ω
Turn-on delay time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 50 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_g = 6 Ω	-	9	20	ns
Rise time	t_r		-	11	20	
Turn-off delay time	$t_{d(off)}$		-	16	30	
Fall time	t_f		-	9	20	
Gate resistance	R_g	V_{GS} = 0.1 V, f = 5 MHz	-	2.8	-	Ω
Source-drain reverse recovery time	t_{rr}	I_F = 1.7 A, di/dt = 100 A/µs	-	50	80	ns

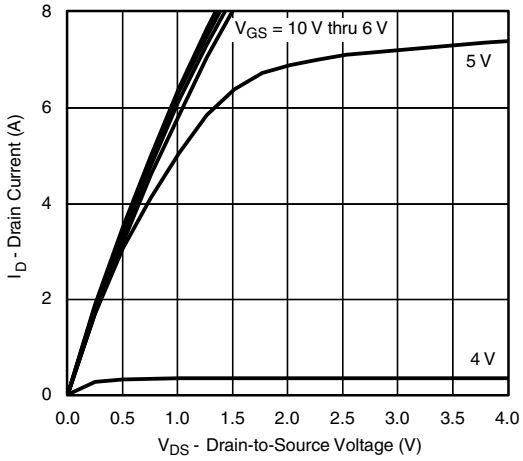
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %

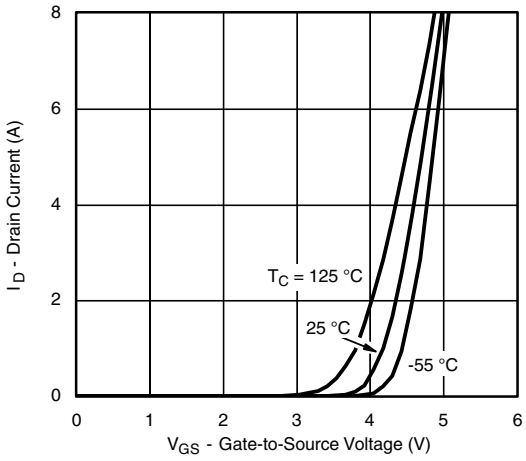
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

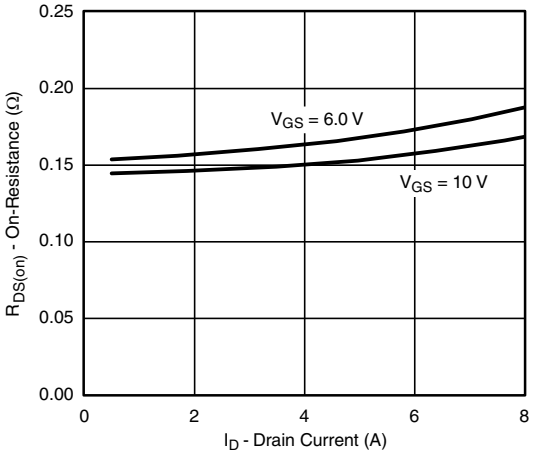
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



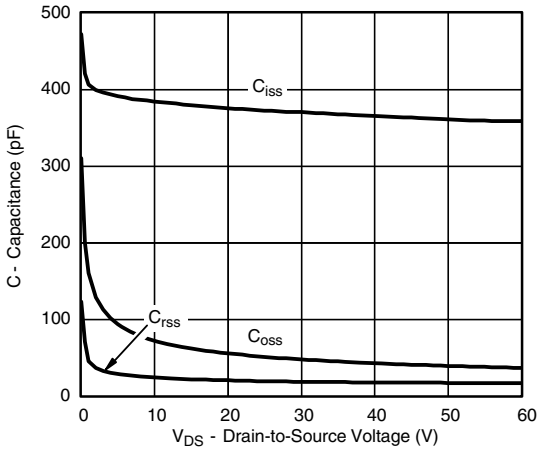
Output Characteristics



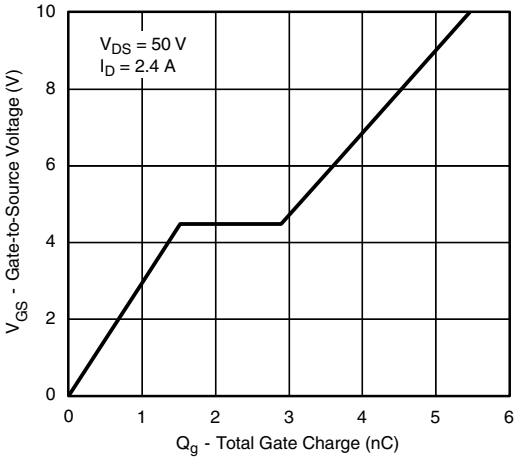
Transfer Characteristics



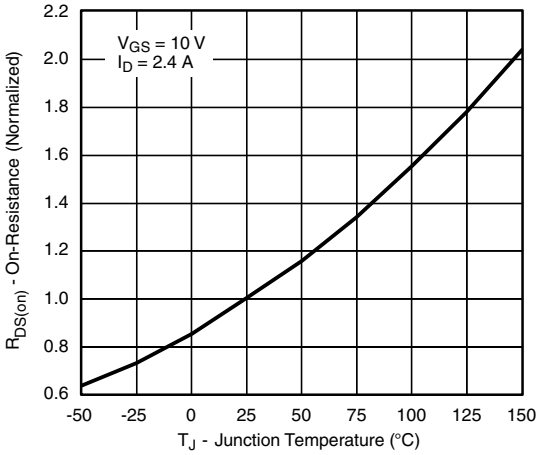
On-Resistance vs. Drain Current



Capacitance

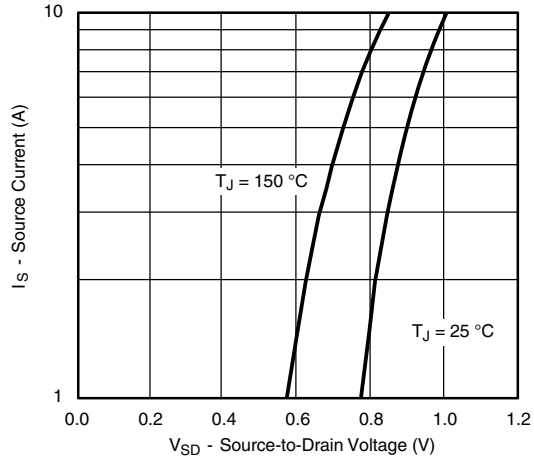


Gate Charge

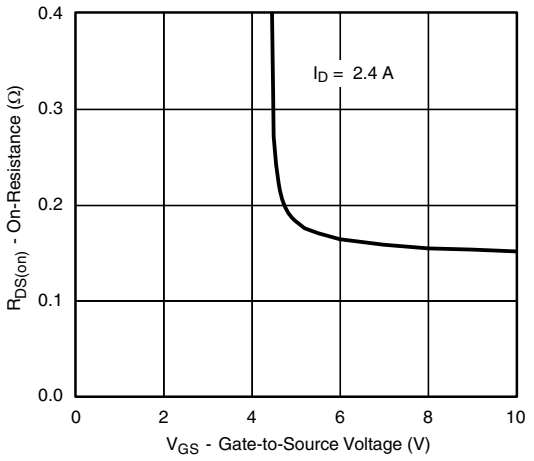


On-Resistance vs. Junction Temperature

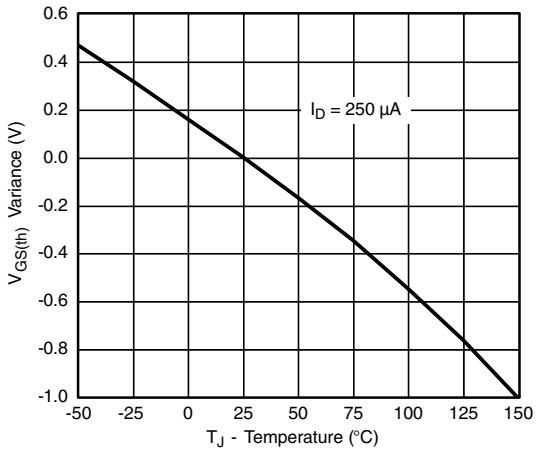
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



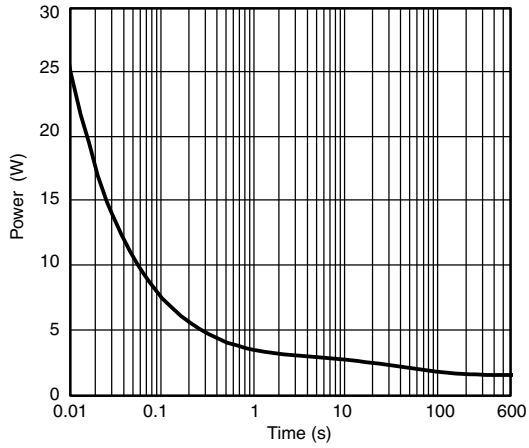
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

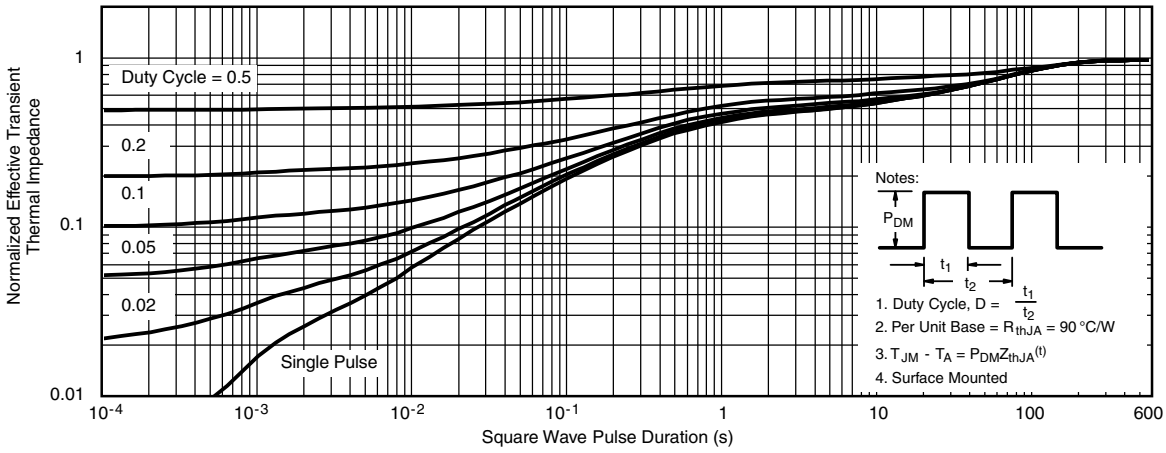


Threshold Voltage

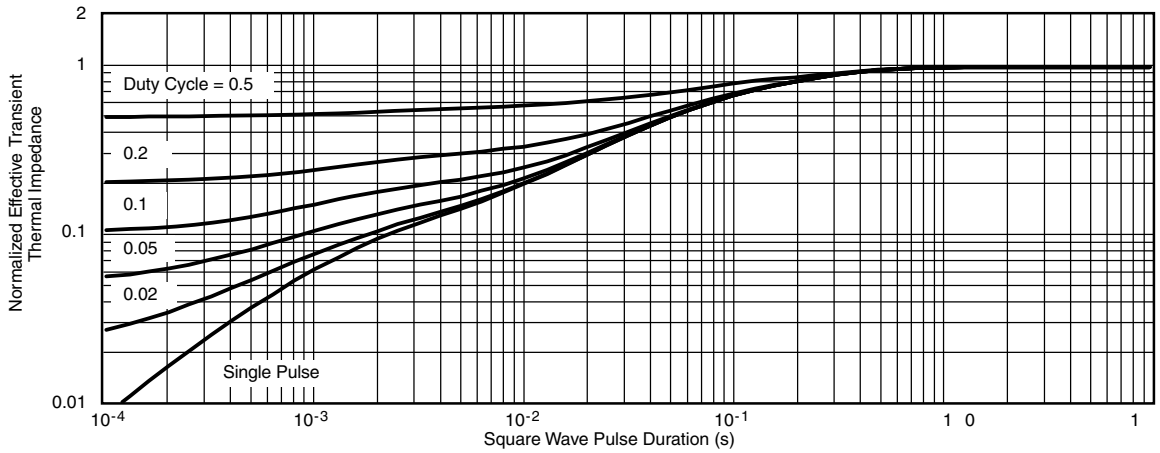


Single Pulse Power

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



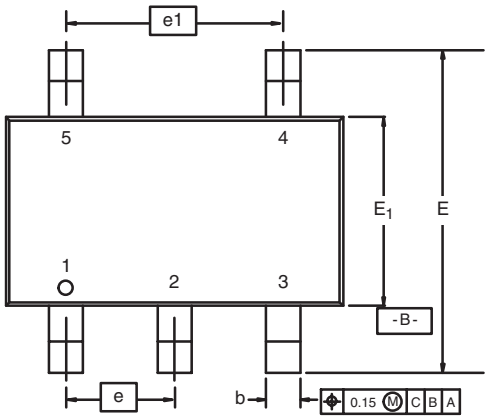
Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71235.

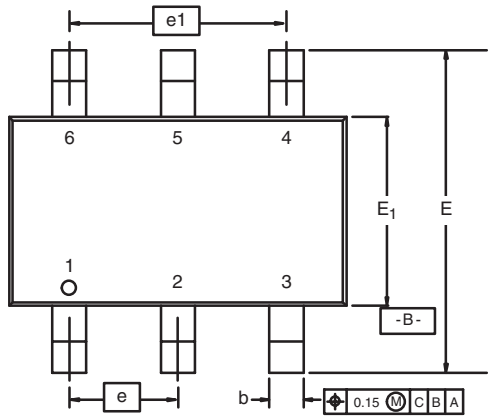
Package Information

Vishay Siliconix

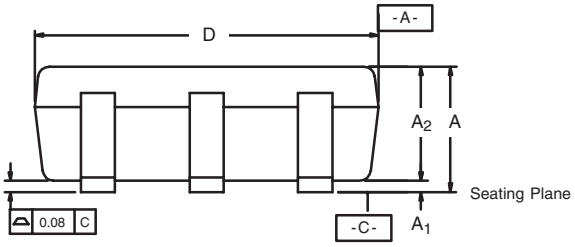
TSOP: 5/6–LEAD
JEDEC Part Number: MO-193C

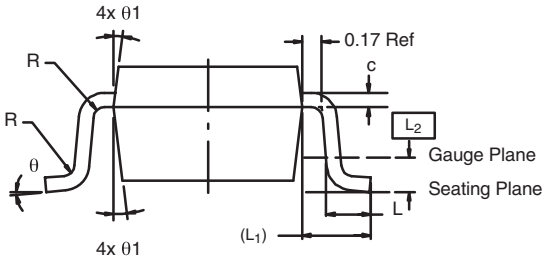


5-LEAD TSOP



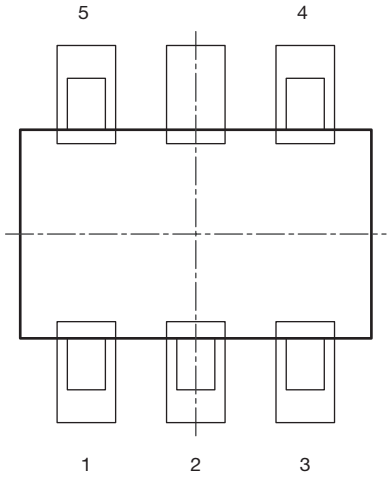
6-LEAD TSOP



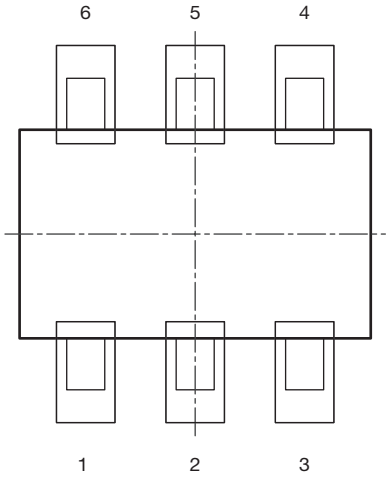


Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A_1	0.01	-	0.10	0.0004	-	0.004
A_2	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E_1	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e_1	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L_1	0.60 Ref			0.024 Ref		
L_2	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

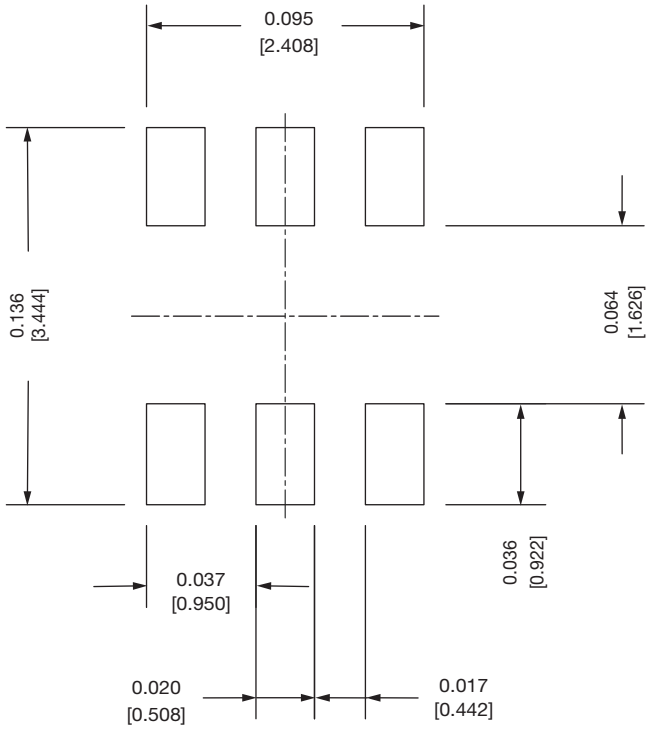
Recommended Land Pattern For TSOP-5L / TSOP-6L



TSOP 5L



TSOP 6L



Note

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010

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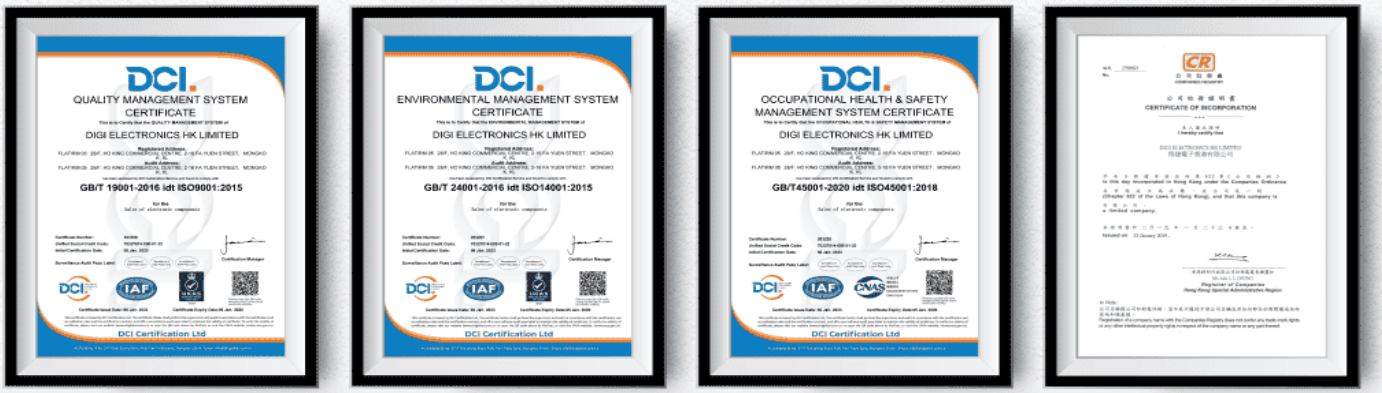

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